

### Supporting information

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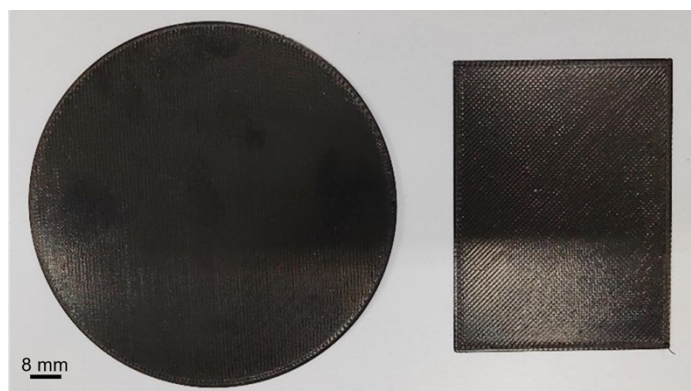
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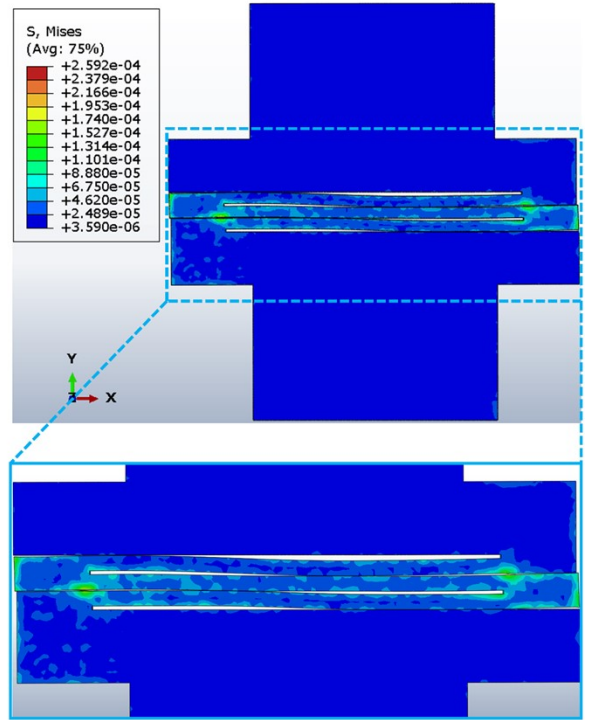
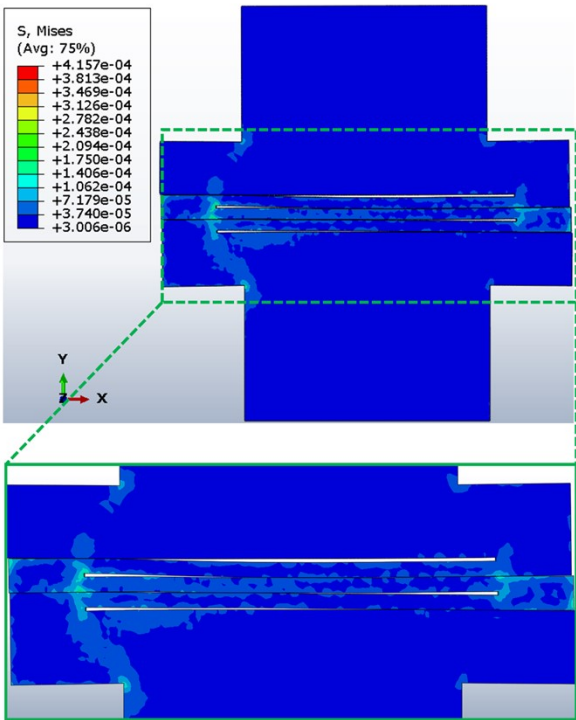
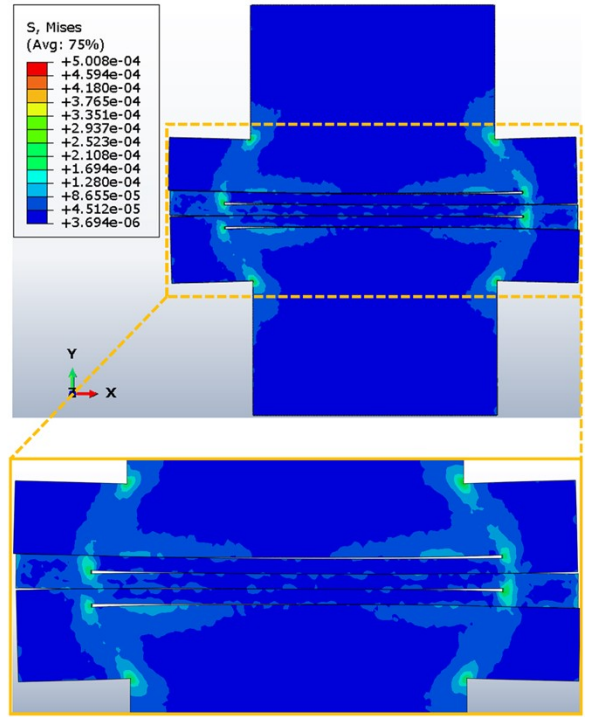
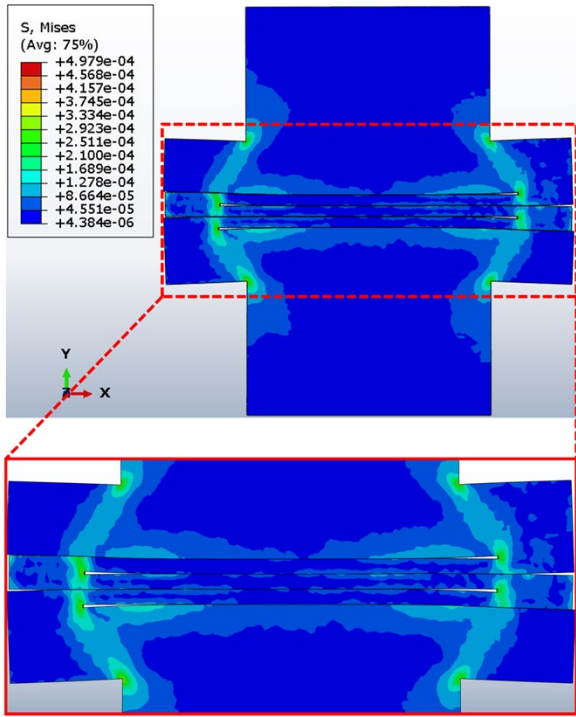
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**Figure S1.** Image of 3D printing conductive films with thickness of 0.5 mm before cutting.

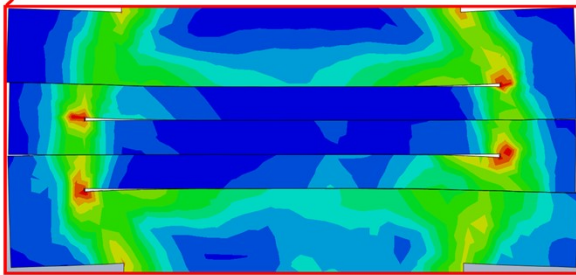
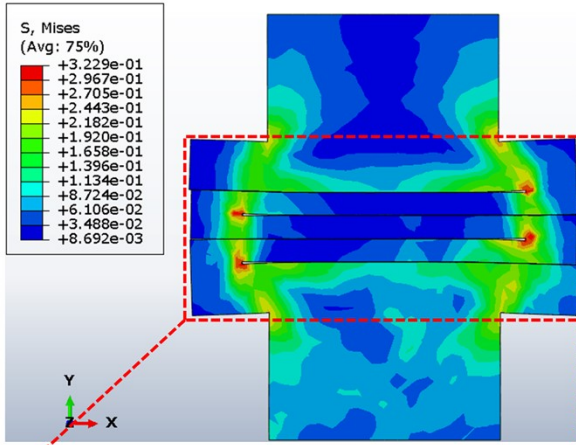
(a)



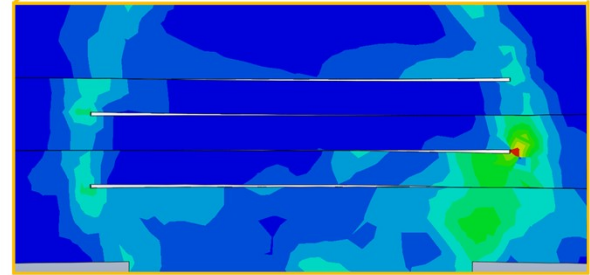
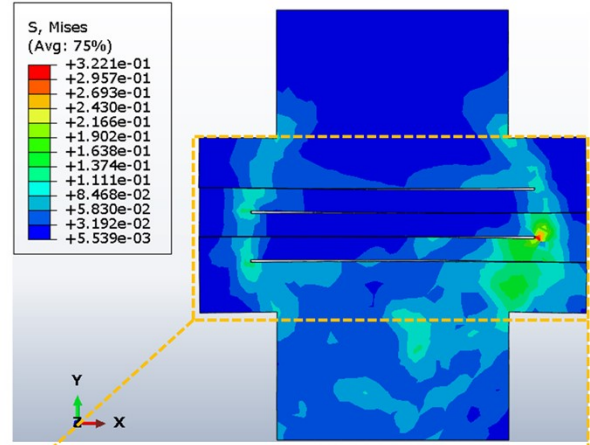
10% strain

15% strain

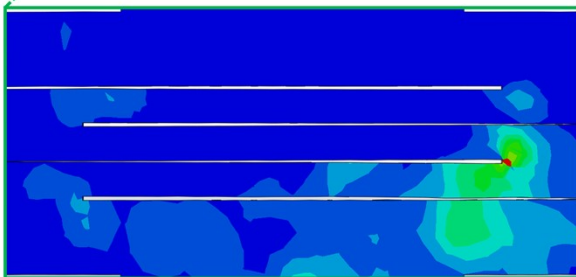
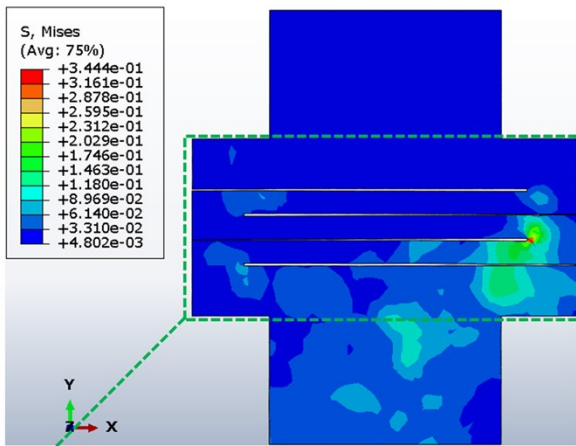
(b)



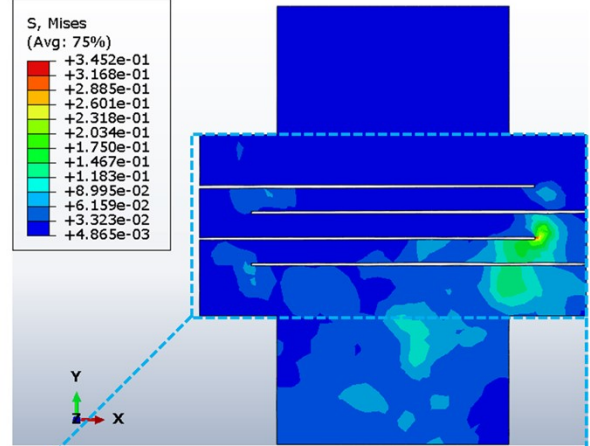
0% strain



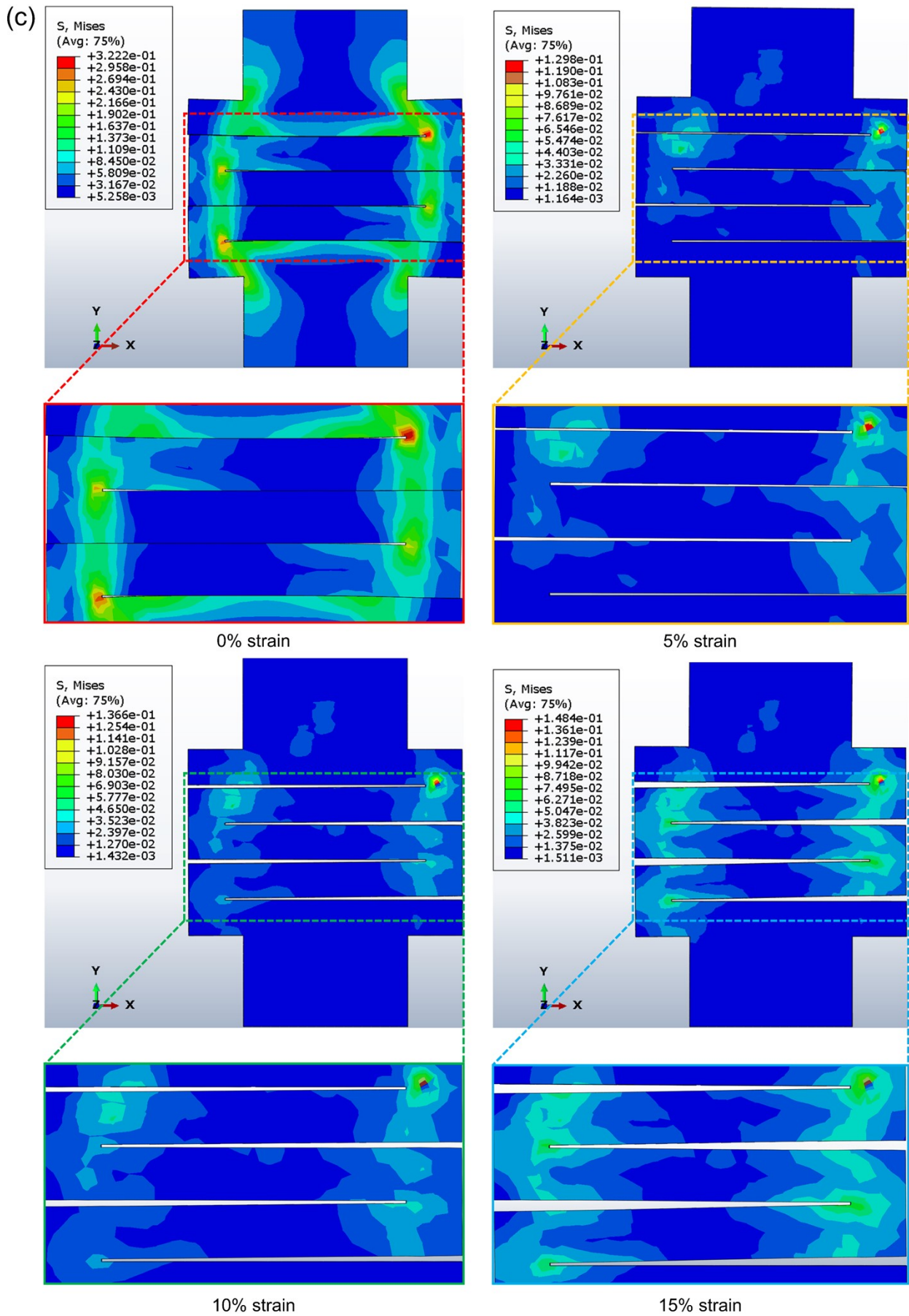
5% strain



10% strain

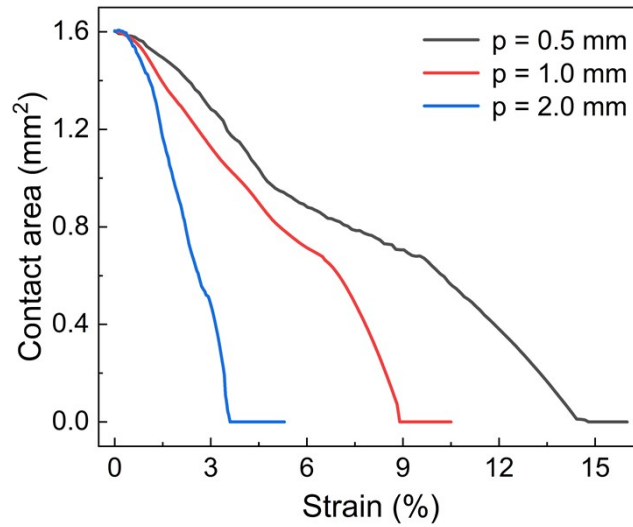


15% strain



**Figure S2.** FEM analysis of strain sensors with different cutting pitch lengths between serpentine curves ( $p$ ). a) The states of the sensor with  $p = 0.5$  mm at 0% strain, 5% strain, 10% strain and 15%

strain. b) The states of the sensor with  $p = 1$  mm at 0% strain, 5% strain, 10% strain and 15% strain.  
c) The states of the sensor with  $p = 2$  mm at 0% strain, 5% strain, 10% strain and 15% strain.

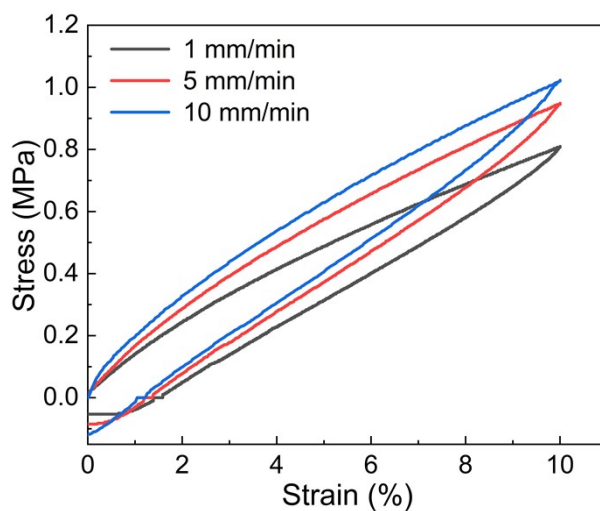


**Figure S3.** Corresponding contact area of one crack for the strain sensors with different cutting pitch lengths between serpentine curves ( $p$ ) based on Figure S2.

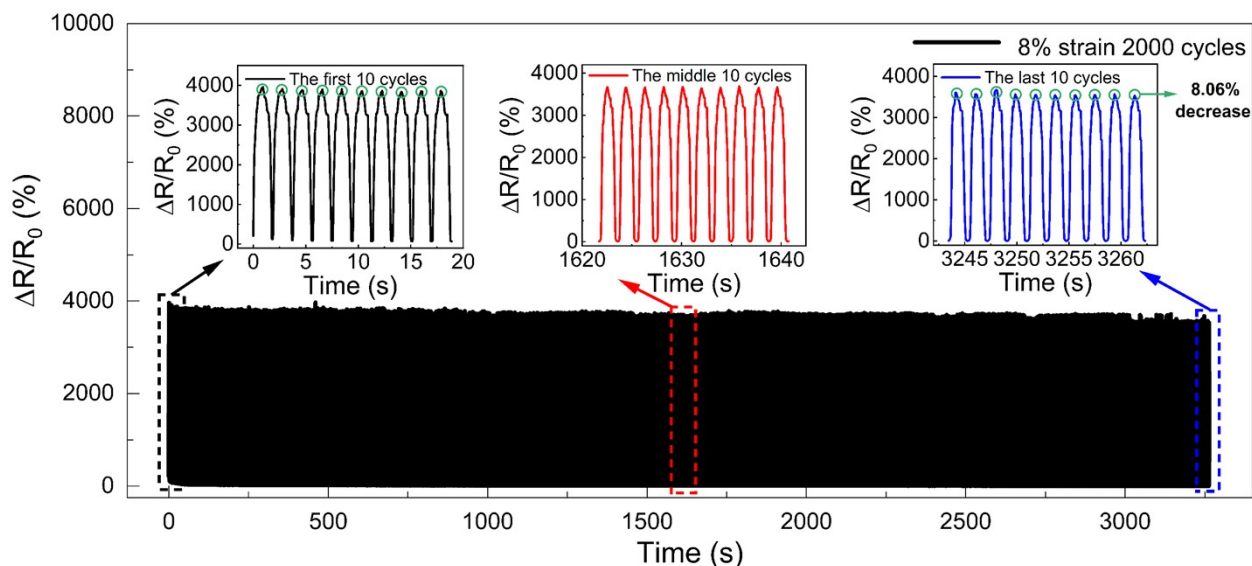
Table S1 Comparisons with previous works in sensing mode

Transducing materials	Sensing modes	Gauge factor	Working range	Resistance relation to strain	Off-axis mode rejection	Temperature rejection	Reference
EGaIn	Strain	4.91	320%	Non-linear	Not shown	Insensitive to temperature (20~80°C)	[1]
MWCNT	Strain	56	70%	Non-linear	Insensitive to pressure	Not shown	[2]
rGo & Nano fiber	Strain	1.6(~10%) ; 7.1(~100%) )	100%	Non-linear	Not shown	Not shown	[3]
AgNWs	Strain	7.5(~40%) ; 12(~100%) )	100%	Non-linear (Two linear regions)	Not shown	Temperature changes by applying strain	[4]
Conductive yarns	Strain	49.5	100%	Linear	Insensitive to pressure and bending	Insensitive to temperature (23.2~40.1°C)	[5]
Nanographene	Strain	325	0.4%	Linear	Not shown	Not shown	[6]
CNT	Strain	8~207	50%	Non-	Not	Not shown	[7]

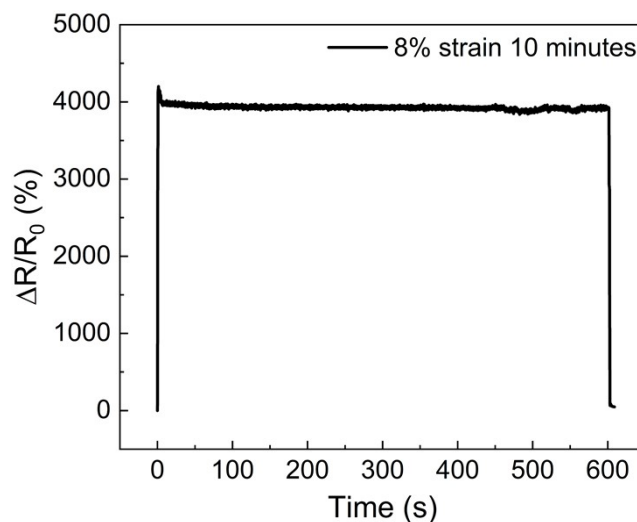
				linear (Three linear regions)	shown		
Conductive Composite Hydrogels	Strain & Pressur e	3.4	300%	Linear		Not shown	[8]
Graphene composite	Strain & Pressur e	<15	100%	Non- linear (Three linear regions)		Not shown	[9]
Conductive TPU	Strain	500	10%	Linear	Insensitiv e to pressur e, bending and twisting	Insensitive to temperature (20~80°C)	This work



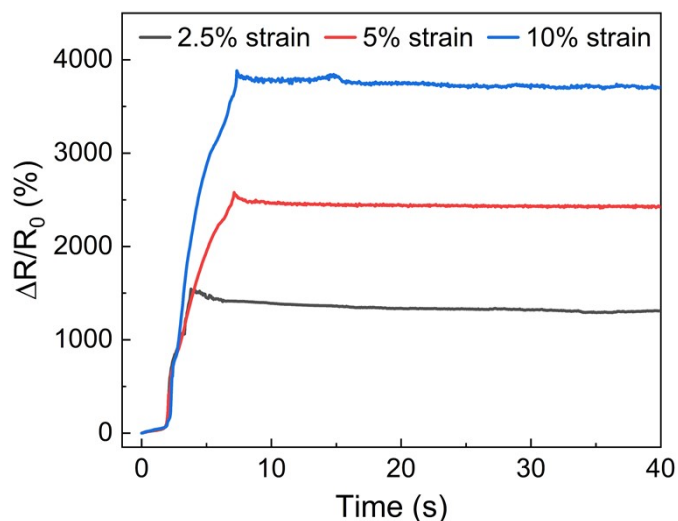
**Figure S4.** The mechanical hysteresis of the sensor under varying stretching speeds of 1 mm/min, 5 mm/min, and 10 mm/min



**Figure S5.** Sensor stability study over 2000 cycles at peak strain of 8%. The insets showing the first 10 cycles, middle 10 cycles, and last 10 cycles, respectively.



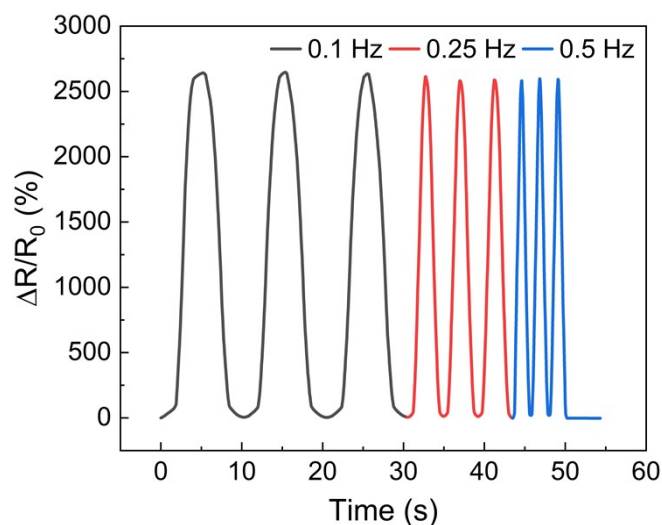
**Figure S6.** The resistance response of the sensor when subjected to a static 8% strain for more than 10 minutes.



**Figure S7.** The relative resistance change of the sensor with a step strain to show low creep and hysteresis.



static stability.



**Figure S8.** Dynamic stability of the sensor at various frequencies ranging from 0.1 to 0.5 Hz.

#### References:

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